

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
ATTY. DOCKET NO.
061282-0234SERIAL NO.
10/574,863APPLICANT
Yuichiro SASAKI, et al.

(Substitute for form 1449/PTO)

FILING DATE
April 06, 2006GROUP
2823**U.S. PATENT DOCUMENTS**

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	US	5,915,196	06-22-1999	MINEJI	
	US	6,163,524	11-28-2000	HENLEY et al.	
	US	6,159,810	12-12-2000	YANG	
	US	2002/0112951 A1	08-22-2002	FAN	
	US	5,407,845	04-18-1995	NASU et al	Corresponds to JP 2530990 B2
	US	5,956,581	09-21-1999	YAMAZAKI et al.	
	US	5,892,235	04-06-1999	YAMAZAKI et al.	
	US	5,915,196	09-21-1999	MINEJI	
	US	6,163,524	11-28-2000	HENLEY et al.	
	US	6,159,810	12-12-2000	YANG	
	US	2002/0112951 A1	08-22-2002	FAN	
	US	6,013,332	01-11-2000	Goto et al.	
	US	6,583,018 B1	06-24-2003	Matsunaga et al.	
	US	6,013,332	01-11-2000	GOTO et al.	Corresponds to JP 10-163123

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -Number + Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No
		WO 03/014979 A	02-20-2003	APPLIED MATERIALS, INC.		X
		JP 2530990 B2	09-04-1996	FUJITSU LTD	Corresponds to US 5,407,845	X
		JP 03-218638	09-26-1991	SEIKO INSTR INC		JAPAN (w/English Abstract)
		JP 6-89904	03/29/1994	SEMICONDUCTOR ENERGY LAB		JAPAN (w/ English Abstract)
		JP 10-163123	06/19/1998	FUJITSU LTD; KAGAKU GIJUTSU SHINKO JIGYODAN	Corresponds to US 6,013,332	JAPAN (w/ English Abstract)

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
		International Search Report issued in International Patent Application No. PCT/JP2005/009949 dated July 5, 2005	
		International Search Report issued in International Patent Application No. PCT/JP2004015308 mailed January 18, 2005	
		Japanese Notification of Reasons for Refusal, w/ English translation thereof, issued in Japanese Patent Application No. JP 2005-502685 dated May 19, 2009	
		European Search Report issued in European Patent Application No. EP 04710478 dated May 12, 2009	
EXAMINER		DATE CONSIDERED	

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	US	2002/0006689 A1	01-17-2002	MIYASAKA, MITSUTOSHI	

FOREIGN PATENT DOCUMENTS

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		JP 7-142421	06-02-1995	NIPPON ELECTRIC CO		JAPAN (w/English Abstract)
		JP 2003-86529	03-20-2003	DENSO CORP		JAPAN (w/English Abstract)
		JP 2003-7636	01-10-2003	SONY CORP		JAPAN (w/English Abstract)
		JP 8-279475	10-22-1996	MURATA MANUFACTURING CO		JAPAN (w/English Abstract)
		JP 2000-12481	01-14-2000	APPLIED MATERIALS INC		JAPAN (w/English Abstract)
		JP 2004-14878	01-14-2000	SHARP KK		JAPAN (w/ English Abstract)
		JP 2004-158627	06-03-2004	RENESAS TECH CORP; ION ENGINEERING RESINTECH CORP; TSUBOUCHI NATSUO		JAPAN (w/ English Abstract)

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		TSUTSUI, K., et al., "Contribution and Control of Neutral Gas Absorption Effects in the Plasma Doping of Boron into Si", 2004, pages 46-49, IEEE.
		BAEK, S., et al., "Characteristics of Low-Temperature Preannealing Effects on Laser-Annealed P+N and N+P Ultra-Shallow Junctions", 2004, pages 54-57, IEEE.
		SEMICONDUCTOR APPLICATIONS, MICROCAVITY ENGINEERING, TRENCH DOPING, pages 662-667
		R. SIEGELE, et al., "Helium Bubbles in silicon: Structure and optical properties," Appl. Phys. Lett. 66 (11), 13 March 1995, pp. 1319-1321
		V.F. REUTOV & A.S. SOKHATSKII, "Helium Ion Bombardment Induced Amorphization of Silicon Crystals," Technical Physics Letters, Vol. 38, No. 7, 2002, pp. 615-617
EXAMINER		DATE CONSIDERED

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